TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE (PCT PROCESS)

2SB906

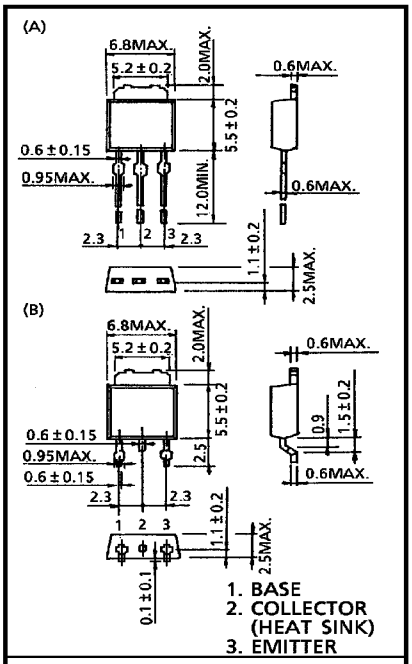
AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

Unit in mm

- Low Collector Saturation Voltage
  : $V_{CE\ (sat)} = -1.0$ V (Typ.) ($I_C = -3$ A, $I_B = -0.3$ A)
- High Power Dissipation : $P_C = 20$ W (Tc = 25°C)
- Complementary to 2SD1221

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	−60	V
Collector-Emitter Voltage		V_{CEO}	−60	V
Emitter-Base Voltage		V_{EBO}	−7	V
Collector Current		I_C	−3	A
Base Current		I_B	−0.5	A
Collector Power Dissipation	Ta = 25°C	P_C	1.0	W
	Tc = 25°C		20	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

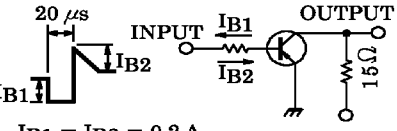


JEDEC	—
EIAJ	—
TOSHIBA	(A) 2-7B1A (B) 2-7B2A

Weight : 0.36 g

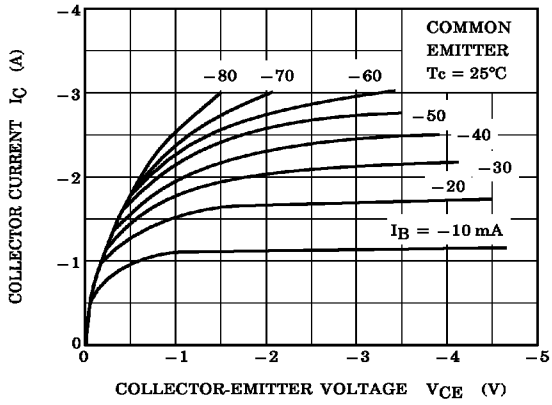
961001EAA1

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

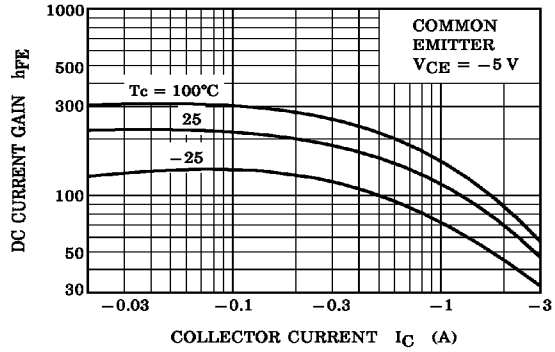
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -60$ V, $I_E = 0$	—	—	−100	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -7$ V, $I_C = 0$	—	—	−100	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)\,CEO}$	$I_C = -50$ mA, $I_B = 0$	−60	—	—	V
DC Current Gain		$h_{FE\,(1)}$ (Note)	$V_{CE} = -5$ V, $I_C = -0.5$ A	60	—	200	
		$h_{FE\,(2)}$	$V_{CE} = -5$ V, $I_C = -3$ A	20	—	—	
Collector-Emitter Saturation Voltage		$V_{CE\,(sat)}$	$I_C = -3$ A, $I_B = -0.3$ A	—	−1.0	−1.7	V
Base-Emitter Voltage		V_{BE}	$V_{CE} = -5$ V, $I_C = -0.5$ A	—	−1.0	−1.5	V
Transition Frequency		f_T	$V_{CE} = -5$ V, $I_C = -0.5$ A	—	9	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz	—	150	—	pF
Switching Time	Turn-on Time	t_{on}		—	0.4	—	μs
	Storage Time	t_{stg}		—	1.7	—	
	Fall Time	t_f		—	0.5	—	

Note : h_{FE} Classification O : 60~120, Y : 100~200

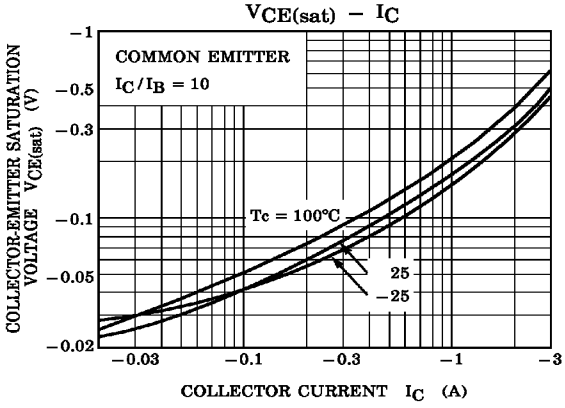
I_C – V_{CE}



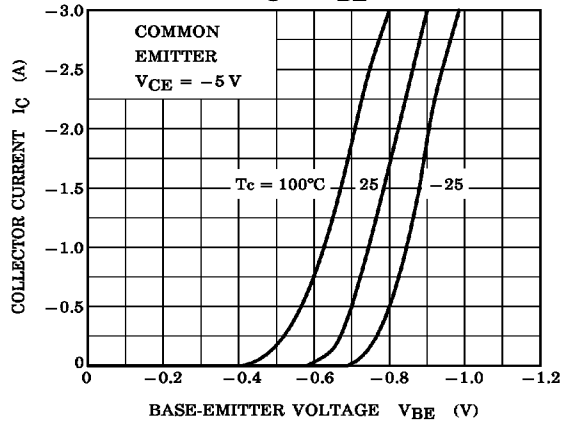
h_{FE} – I_C



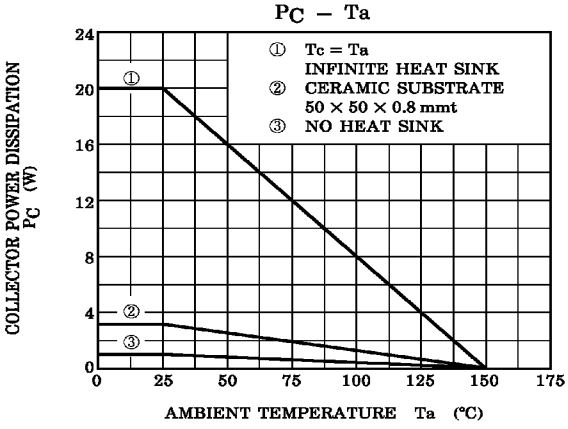
$V_{CE(sat)}$ – I_C



I_C – V_{BE}



P_C – Ta



SAFE OPERATING AREA